

The **ARCADIA** Depleted Monolithic Active Pixel: characterization and prospects for high precision tracking systems at future colliders

Davide Chiappara^{1,2}, Sabrina Ciarlantini², Piero Giubilato^{1,2}, Serena Mattiazzo^{1,2}, Devis Pantano^{1,2}, **Caterina Pantouvakis**^{1,2}, Michele Rignanese^{1,2}, Alessandra Zingaretti²

¹Istituto Nazionale di Fisica Nucleare, Sezione di Padova, Via Marzolo 8, 35131 Padova ²Università degli Studi di Padova, Dipartimento di Fisica e Astronomia, Via Marzolo 8, 35131 Padova

Future tracker detectors

The main requirements for vertex detectors and trackers of experiments at future colliders are high momentum and spatial resolution, and to perform non perturbative measurements.

Monolithic Active Pixel Sensors (MAPS) have recently gained interest

Sensor characterization: exploiting X-rays

One of the possible characterization studies of digital MAPS is related to threshold calibration.

The standard way is based on analog injection, however a different approach is to use monochromatic X-ray sources, performing measurements varying the pixel threshold \rightarrow S-curve.

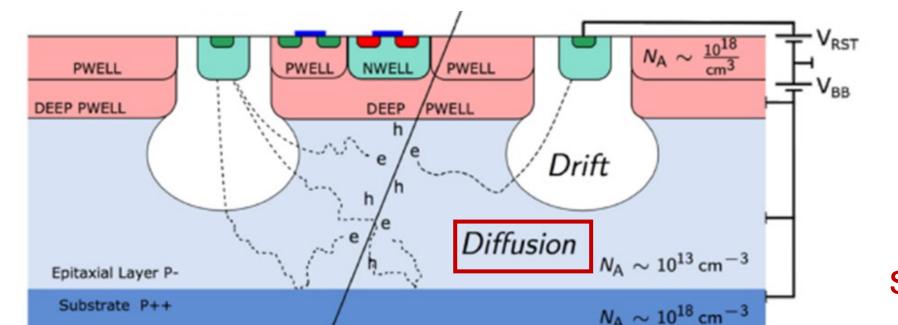
for inner trackers and vertex detectors, because of their features:

small pixel pitch ✓ thin, bent and stitched sensors \checkmark low power, material budget, production costs </

MAPS-based ePIC barrel vertex end endcap detectors at the Electron-Ion Collider EIC (BNL)

> Next generation 65-nm reticle-size bent MAPS

Typical MAPS cross section

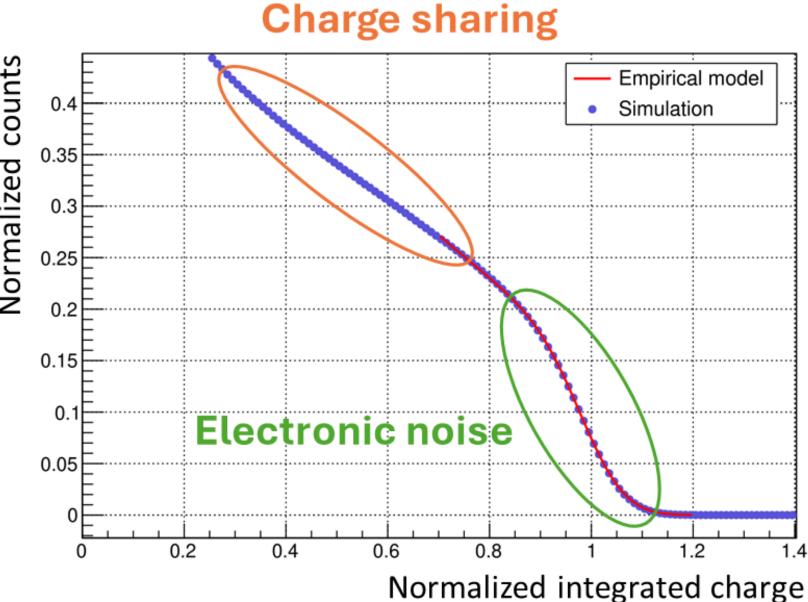


MAPS drawbacks: Charge is collected mainly by diffusion slow collection

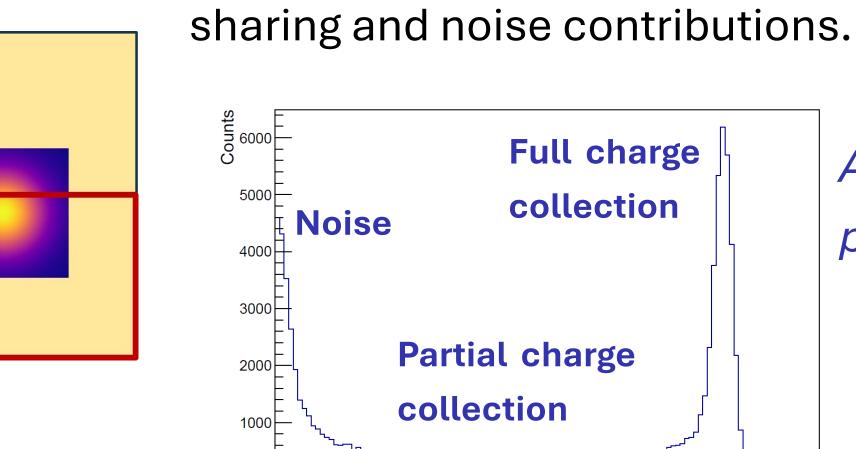
[1]

Χ

The **S-curve** shape, obtained with analog injection, decount pends only on the pixel electronic noise. However, when the S-curve is acquired with Ž a monochromatic source, an additional linear contribution arises due to charge sharing effects.



A MonteCarlo simulation has been developed to study geometrical charge sharing among pixels and to extract estimations on the charge



Analog simulated pixel spectrum

FRENT

low radiation hardness **x**



[2]

The drawbacks mentioned above can be partially overcome by recent **Depleted MAPS (DMAPS)** in which the depleted region is extended to the full silicon substrate.

In this way, charge is collected mainly by drift.

Faster and more efficient collection ✓

Improved radiation hardness ✓

An example is the **ARCADIA** chip (MD3), a 512x512 pixel array, with an active area of 1.28×1.28 cm². It has been fully designed and manifactured by the INFN Arcadia collaboration and LFoundry.



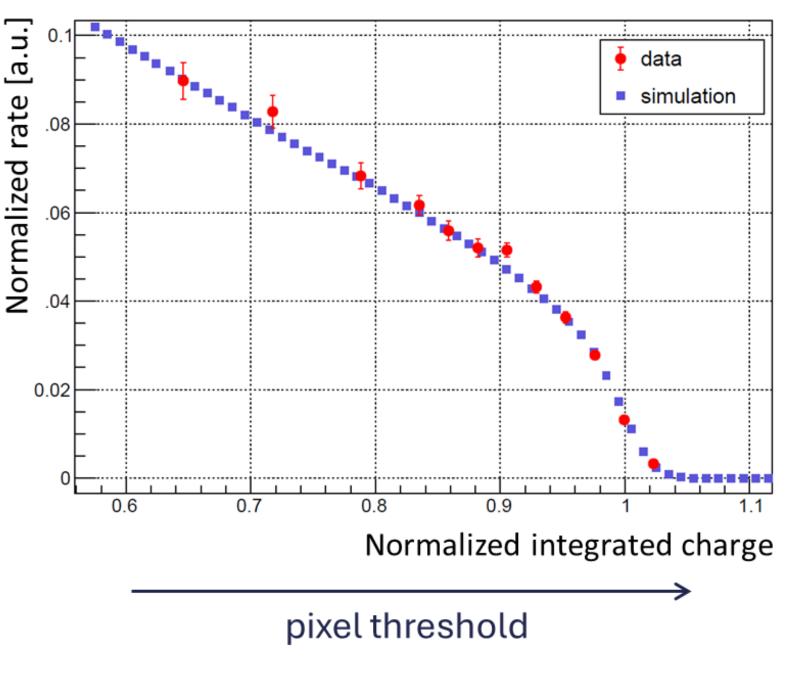
Technology

CIS 110 nm

S-curve measurements and comparison

with simulation

Measurements have been performed with ⁵⁵**Fe** source (~ 5.9 keV): single pixel hit rate at different values of threshold is compared with simulation.



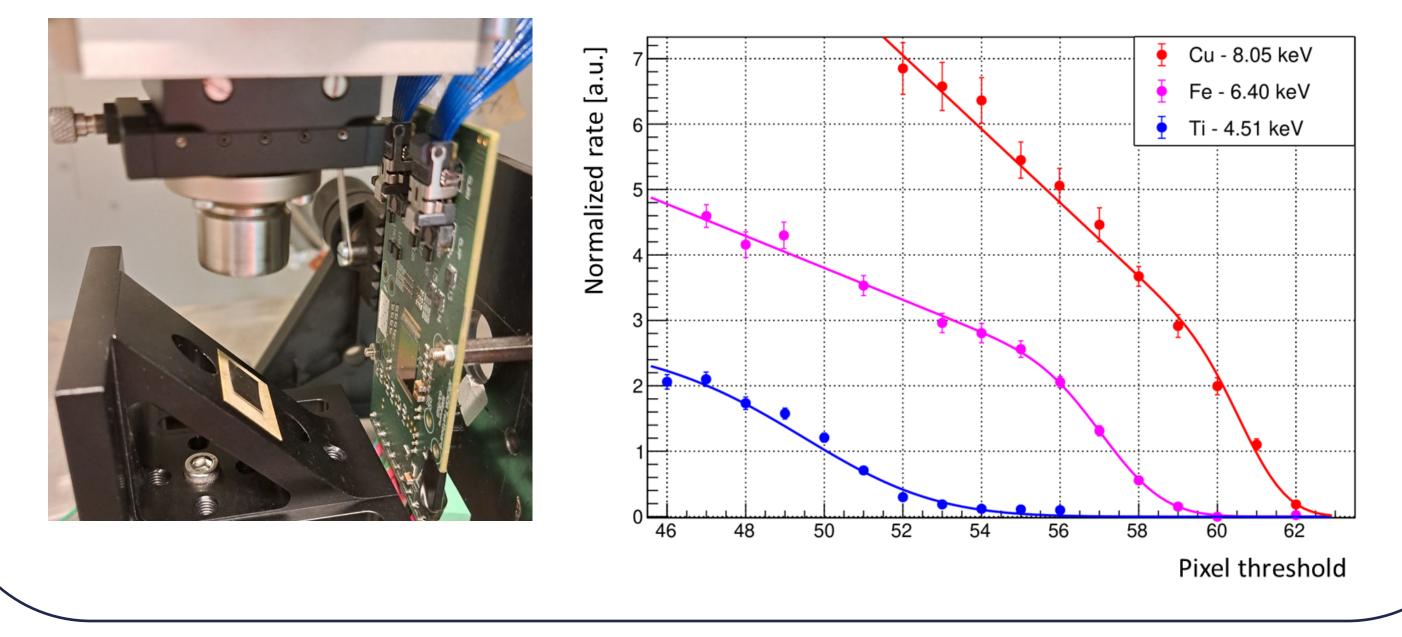
Ongoing work

To study the response at different energies, it is possible to perform measurements with **X-ray fluorescence**, obtained using a primary X-ray beam and different target materials.



Pixel pitch 25 µm Power consumption $O(10 \text{ mW/cm}^2)$ Digital Readout

Peripheral Pixel array electronics deep pwell n-epi n-senso 50-200 µm fully depleted High-Resistivity Substrate Drift (DMAPS) active substrate n-sub [3]



[1] D. Elia, Update on Silicon Tracker, EIC_NET National Meeting (2023)

[2] ALICE Collaboration, Letter of intent for ALICE 3: A next-generation heavy-ion experiment at the LHC (2022)

[3] T. Corradino et Al., Design and Characterization of Backside Termination Structures for Thick Fully-Depleted MAPS, Sensors, 21 (2021)